

## **Investigation of contact line motions of EGaln for microstructure fabrication**

\*Sangyun Jung<sup>1)</sup> and Wonjung Kim<sup>2)</sup>

<sup>1), 2)</sup> *Department of Mechanical Engineering, Sogang University, Seoul 04107, South  
Korea*

<sup>2)</sup> [wonjungkim@sogang.ac.kr](mailto:wonjungkim@sogang.ac.kr)

### **ABSTRACT**

Eutectic gallium-indium (EGaln) are attracting growing attention in various engineering fields thanks to their combined properties of fluidity and high electrical conductivity. EGaln has an oxide skin in the atmosphere with nanometer thickness, and the oxide skin results in unique interfacial behaviors. Although the oxide skin is a key factor for controlling the motions of EGaln at a microscale, the interfacial physics of EGaln has been little explored. Here, we present the results of investigation of the effective surface tension and contact angle of EGaln with the oxide skin. Our experiments revealed that the effective surface tension depends on oxide wrinkle and showed that while the equilibrium and receding contact angles cannot be defined, a specific advancing contact angle is observed in EGaln motion. We then develop a mathematical model for the advancing contact angle of EGaln. Our study provides new insights into the manufacturing techniques of EGaln for microscale electronic components.

---

<sup>1)</sup> Graduate Student

<sup>2)</sup> Professor